NSN 5961-01-298-0239



Diode Semiconductor Device - Page 1 of 1

View Online at https://aerobasegroup.com/nsn/5961-01-298-0239
Inclosure Material:
Glass
Overall Length:
Between 0.140 inches and 0.185 inches
Terminal Length:
Between 1.000 inches and 1.300 inches
Overall Diameter:
Between 0.085 inches and 0.140 inches
Function For Which Designed:
Transient suppressor
End Application:
An/aar-44 infrared system
Mounting Method:
Terminal
Features Provided:
Hermetically sealed case and quality assurance level txv
Semiconductor Material:
Silicon
Voltage Rating In Volts Per Characteristic:
43.0 breakdown voltage, dc and 32.7 working peak reverse voltage
Voltage Tolerance In Percent:
-5.0/+5.0
Current Rating Per Characteristic:
30.00 milliamperes collector current, dc horsepower metric and 5.00 microamperes forward current, average peak
Power Rating Per Characteristic:
3.0 watts small-signal input power, common-collector major
Maximum Operating Tempurature Per Measurement Point:
175.0 degrees celsius ambient air
Test Data Document:
81349-mil-s-19500 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification
format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain
environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.).
Terminal Type And Quantity:
2 uninsulated wire lead
Specification Data:
81349-mil-s-19500/516 government specification
Shelf Life:
N/a
Unit Of Measure:

Demilitarization:

No

Fiig:

A110a0